NSN 5961-00-018-9118

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View Online at https://aerobasegroup.com/nsn/5961-00-018-9118 **Inclosure Material:** Metal **Overall Length:** 0.310 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 breakover voltage, dc **Current Rating Per Characteristic:** 5.00 amperes source cutoff current **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 80131-release5221 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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